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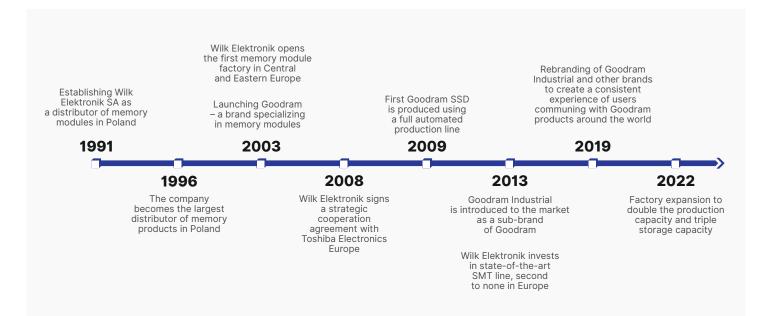


About the Company

Goodram Industrial is a brand owned by Wilk Elektronik SA – a Polish memory manufacturer and distributor with over 30 years of experience in the memory business.

Known for its strict quality policy, flexibility and post-sales support, Wilk Elektronik SA is the only European memory manufacturer with its own lab, R&D department, state-of-the-art production site, test field and support team. All in-house, under one roof.

Goodram stands for quality, reliability and support – we believe that the industry needs customized solutions for very specific needs. Designing our own testing procedures ensures that the modules we produce are tailored to match our customers' needs perfectly. Add low MOQ, fixed BOM and long-term post-sales support to the mix to achieve the highest possible quality of customer service. It all boils down to guaranteeing our partners the highest reliability possible throughout the module's lifetime.



How we work

To put it briefly, we consider your needs and do everything we can to provide you with the perfect product to do the job. Every case is a different story of satisfying very specific needs by providing a dedicated, customized and reliable solution. And in our minds "solution" is not only the final module or memory card your company uses. The solution is everything that happens before, throughout the ordering process and after the sale.

Services

Every customer brings different needs and expectations to the table. It's in our company's DNA to react to those dynamically changing variables. We provide services that go far beyond a simple sales process:

- pre-sales support which includes meticulous interviews with the customer, giving us a greater understanding of our partner's needs;
- complex customer service throughout the sales process, which means making sure we have a specific solution available for you over a long period of time among other things;
- post-sales support, such as diagnostics, consulting and training.

Quality assurance

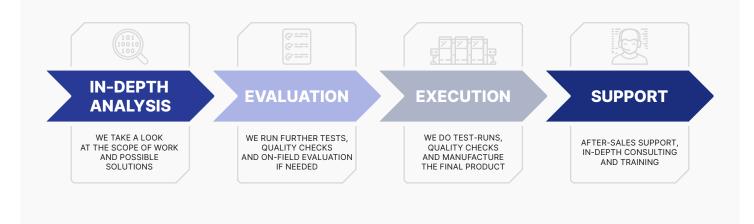
Everything we do is oriented towards providing products of the highest quality.

Quality, as we understand it, means complete reliability and satisfaction of the customer's requirements throughout the product's lifetime. It's the reason why we continuously invest in more advanced machinery, diagnostic equipment and people, who create our LAB, R&D and QC departments. The more complicated cases and issues w solve throughout our design and production processes, the harder we believe this is the right course to take. Constant growth and evolution is the key to our success.

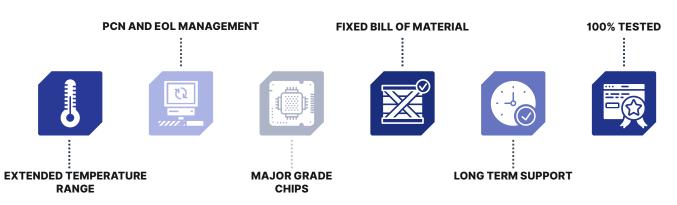




There are four simple steps we take in every project we are involved in:



CORE FEATURES





Applications of Goodram Industrial solutions



HOME AUTOMATION

Home automation systems are innovative technologies that are getting more popular every day. Setting up your own way to shape and operate within the environment you live in creates more and more need for memory products.

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POINT-OF-SALE (POS)

A point-of-sale terminal is an essential part of every modern store. In many cases, to conform with local law, transactions are recorded in the terminal's memory. More and more POS are equipped with NAND flash storage.

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INTERNET OF THINGS

The "Internet of Things" is the future that we are just entering. Continuous and seamless communication of devices around us creates new demand within storage and data transfer technologies.



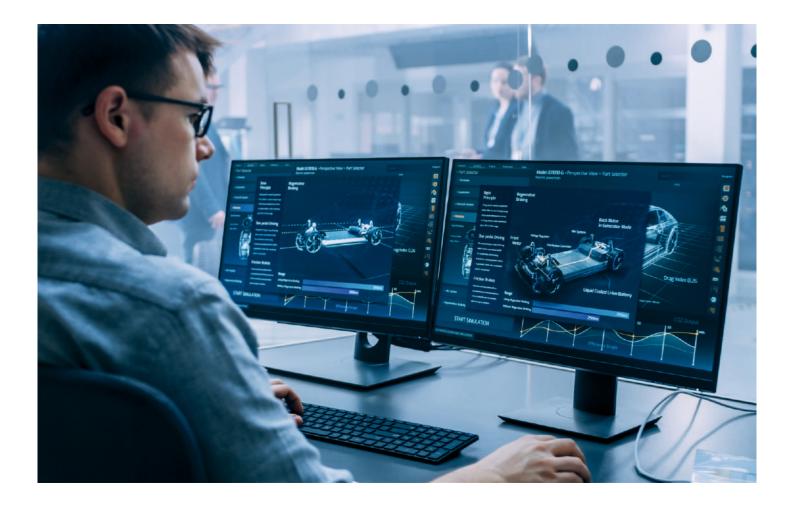
INDUSTRIAL COMPUTING

Supervising production processes is no longer exclusively a human domain. They can be successfully controlled by intelligent computer systems that make them more efficient.



VIDEO SECURITY SYSTEMS

The use of CCTV systems is more and more popular in all fields of human activity. Whole cities, events and large production plants are being monitored and those videos are recorded for safety measures - which creates the need for faster, more reliable and durable storage.





INDUSTRIAL AUTOMATION

Meticulous and precise production processes are now performed by automated devices and robots. Their operations are controlled by advanced computer systems.



WIRELESS SYSTEMS

Digitalization of our everyday life requires introduction of new means of communication. They include wireless data transfer systems which enable global access to the resources we all create.



PUBLIC COMMUNICATION

People commute every day, usually to work or school. New technologies can now make means of public transportation faster, more efficient and safer.



AUTOMOTIVE SOLUTIONS

The car is no longer just a simple means of transport. Today, every vehicle is expected to be equipped with a multimedia system and navigation.



HUMAN-MACHINE INTERFACES

These interface devices enable human operators to communicate with machines and collect data from monitored processes. Modern interfaces feature a touch screen and offer a visual display that makes it easy to control processes and receive alerts in case of potential dangers.

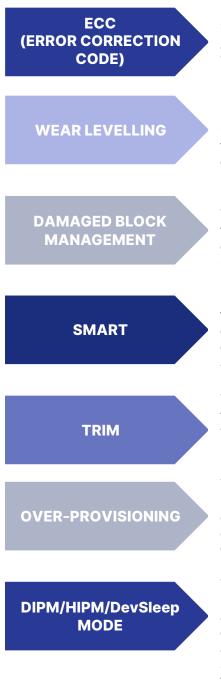
Flash core features

FLASH MEMORY

NAND Flash based memory devices form a distinct group of products with a range of different interfaces and applications. Depending on the type of NAND flash used, these products differ in terms of durability, speed and capacity. All of them, however, have advanced mechanisms to ensure data integrity. We currently offer solutions based on SLC, pSLC, MLC, 3D TLC and 3D pSLC NAND Flash.

NAND FLASH MANAGEMENT

Goodram Industrial storage products utilize the latest technologies to ensure complete reliability up to the specified TBW (Total Bytes Written) value. These technologies include:



NAND Flash memory cells are subject to wear, potentially causing random errors in the stored data. Goodram Industrial implements advanced error detection and correction algorithms (LDPC/BCH) appropriate for the used technology. This guarantees a high level of data security up to the specified TBW.

NAND Flash memories have a limited number of program/erase cycles. To ensure product longevity, data must be evenly distributed between the memory blocks. Goodram Industrial memories implement advanced wear leveling algorithms for this purpose. This means that the fixed flash blocks will not wear out due to repeated writing to a particular address location.

In NAND Flash memory units, certain memory blocks may be rendered unusable. This occurs during manufacturing of the devices and during their subsequent use, for instance as a result of wear. Such blocks must be excluded from use. Methods of fault prediction and exclusion of unusable memory blocks are implemented in all Goodram Industrial Flash products.

SMART (Self-Monitoring Analysis and Reporting Technology) is a technology for self-diagnosis and reporting oriented towards the prediction and detection of basic faults. In the case of SSDs, the self-diagnosis results and wear statistics can be accessed via a standardised interface. In the case of memory cards, such as SD, access to this data requires the use of special software.

TRIM is a command defined by the ATA standard, enabling the operating system to inform the SSD controller which sectors contain expired data, so that the flash wear levelling algorithm does not transfer expired data between blocks. It can significantly increase the lifetime of SSD.

This term refers to the memory capacity not available to the user. Thanks to the limit on available capacity, mechanisms used for organizing the stored data are used less frequently, leading to increased operations per second (IOPS) and reduction in write amplification. This results in faster write speeds and longer device lifetime.

The SATA interface utilizes two reduced power modes: partial and slumber. In partial mode the power consumed by the interface is limited to a few tens of mW and the wake-up time is not more than 10 μ s. In slumber mode the power consumption is further reduced and the wake-up time may be up to 10 ms. Partial and slumber modes may be initiated by the host computer (HIPM) or by the storage device (DIPM). SSDs may also offer a DevSleep mode, resulting drive to go into a deep "device sleep" significantly reducing power consumption. Reduced power modes enable mobile devices to operate for longer without recharging.

CFast

CFast cards are compliant with the PCMCIA I or II standards with SATA interface. The card's controller, which is functionally compliant with typical SATA SSD controllers, offers low power comsumption and data transfer rates of up to 550 MB/s. Other features include S.M.A.R.T., advanced power management methods and a DRAM catche. CFast is available with 3D TLC, 3D pSLC, MLC, pSLC and SLC NAND and its capacity may depend on the technology used. It's small size and housing suited for mutiple applications make CFast a good solution form many mobile applications.



		CFast									
Flash type	3D TLC	3D pSLC	MLC	pSLC	SLC						
Program/Erase cycles	3 000	3 000 50 000 3 000 20 000									
Capacity	128 GB – 512 GB	32 GB – 256 GB	32 GB – 256 GB	16 GB – 64 GB	8 GB – 32 GB						
Interface			SATA III								
Key features		Static and Dynamic Wear Leveling Bad Block Management TRIM S.M.A.R.T. NCQ Over-Provisioning Low Power Management Thermal Sensor TCG Opal Build from major IC grades FIX BOM (optional) PCN and EOL notification									
Operating temperature (°C)	Silver grade: 0 – 70 Diamond grade: -40 – 85	Silver grade: 0 – 70 Diamond grade: -40 – 85	Gold grade	de: 0 - 70 e: -25 - 85 ade: -40 - 85	Gold grade: -25 – 85 Diamond grade: -40 – 85						
Storage temperature (°C)			-40 - 85								
Maximum transfer speed (MB/s)	Read: up to 550 Write: up to 490	Read: up to 550 Write: up to 500	Read: up to 555 Write: up to 465	Read: up to 545 Write: up to 465	Read: up to 540 Write: up to 305						
Maximum power consumption (mW)	< 1 550	< 1 300	< 1 550	< 1 475	< 1 700						
MTBF	> 2 000 000	> 3 000 000		> 2 000 000							
Environmental tests resistance		High/Low temperature High Humidity (55, 95% RH) Temperature Cycle (30 min, 20 cycles) Shock (1 500 G, Half Sin Pulse) Vibration (80 – 2 000 Hz/20 G in 3 Axis) Free Fall (0.8 m) Torque (1.3 N/m, 30 sec/5 times) Bending (>50 N for 1 min/5 times) Contact ESD (±4 KV contact)									
Dimensions ((L × W × H) (mm))			42.8 × 36.4 × 3.3								

CFexpress

CFexpress cards are currently the newest solution supported by Compact Flash Association, which is capable of to fulfill the most rigid demands of industrial customer. By offering excellent performance and wide compatibility, Goodram's CFexpress™ Type B Card also provides a wide range of capacities available for users. In addition, industrial-grade CFexpress™ cards are available for any applications under rigorous environmental conditions including extensive temperature, shock and vibration.



	CFexpress
Flash type	3D TLC
Program/Erase cycles	3 000
Capacity	15 GB – 1024 GB
Interface	PCIe NVMe 3.0 x2
Key features	PCIe NVMe Gen3 x2 Type B Slot Static and Dynamic Wear Levelling LDPC ECC Subpage Mode Flash Translation Layer Data Care Management Lifetime Enhancements Power Fail Data Loss Protection TRIM Active State Power Management Firmware Update S.M.A.R.T TCG Opal (optional) End-to-End Data Protection AES256 Encryption (optional) Build from major IC grades FIX BOM (optional) PCN and EOL notification
Operating temperature (°C)	Diamond grade: -40 – 85
Storage temperature (°C)	-40 - 85
Maximum transfer speed (MB/s)	Read: up to 1 610 Write: up to 820
Maximum power consumption (mW)	< 760
MTBF	> 2 000 000
Environmental tests resistance	High/Low temperature High Humidity (55, 95% RH) Temperature Cycle (30 min, 20 cycles) Shock (1 500 G, Half Sin Pulse) Vibration (80 – 2 000 Hz/20 G in 3 Axis) Free Fall (0.8 m) Torque (1.3 N/m, 30 sec/5 times) Bending (>50 N for 1 min/5 times) Contact ESD (±4 KV contact)
Dimensions ((L × W × H) (mm))	38.5 × 29.6 × 3.8

eMMC

eMMC (Embedded MultiMediaCard) is a type of small memory device used primarily in portable devices. Unlike portable microSD/SD cards or SSDs, the eMMC standard refers to a non-volatile memory chip embedded on the motherboard of a device. An eMMC is a compact storage device that is physically integrated into an application. Due to its small size, it can be successfully used in devices where SSD drives cannot be installed because of limited space. This includes not only mobile phones and tablets, but also advanced automotive and Internet of Things (IoT) applications.



	eMMC										
Form factor		153 Bal	II FBGA								
Flash type	3D TLC	3D TLC 3D pSLC MLC 2D pSLC									
Capacity	16 GB – 128 GB	16 GB – 128 GB 8 GB – 32 GB 8 GB – 16 GB 4 GB – 8 GB									
Program/Erase cycles	3 000	3 000 30 000 3 000 20 000									
Interface		eMM	C 5.1								
Key features		Cache RPMB Throu	Mode available vice Life time d Queuing d Strobe hing Report Control Barrier ught Improve e Protection n commands available ite Protection ajor IC grades (optional) L notification								
Operating temperature (°C)		Diamond gra	de: -40 – 85								
torage temperature (°C)		-40	- 85								
Maximum transfer speed (MB/s)	Read: up to 320 Write: up to 260	Read: up to 320 Write: up to 260	Read: up to 225 Write: up to 140	Read: up to 225 Write: up to 140							
Maximum power consumption (mW)		< 175		< 170							
Dimensions ((L × W × H) (mm))		11.5 × 13 × 1									

microSD/SD

MicroSD and SD cards are available in three capacity standards: SDSC (Standard Capacity), SDHC (High Capacity) and SDXC (extended Capacity) and with bus up to UHS-I. Selected models have an additional SPI interface. Small dimensions, low power consumption and wide range of available capacities (from 128 MB to 256 GB) and wide selection of NAND types (SLC, pSLC, MLC, 3D TLC and 3D pSLC) make microSD and SD cards a go-to storage solution for many industrial designers.

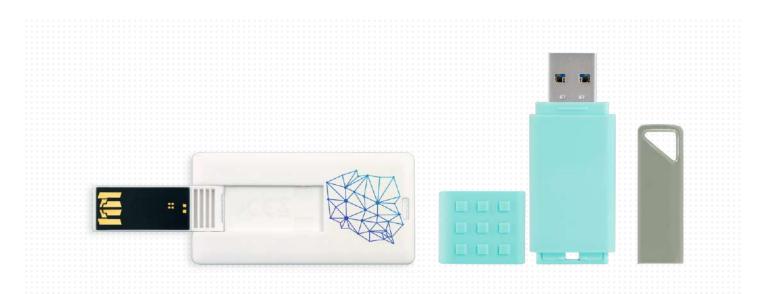




			microSC					SD		
Flash type	3D TLC	3D pSLC	MLC	pSLC	SLC	3D TLC	3D pSLC	MLC	pSLC	SLC
Program/Erase cycles	3 000	30 000	3 000	20 000	60 000	3 000 30 000 3 000 20 000				60 000
Capacity	16 – 256 GB	16 – 128 GB	4 – 64 GB	2 – 32 GB	128 MB – 4 GB	32 – 256 GB	16 – 128 GB	4 – 128 GB	2 – 64 GB	128 MB – 32 G
Interface		High Speed 128 MB – 2 GB 12 for 2 GB High Speed								128 MB – 2 GI High Speed 4 GB – 32 GE UHS-I
Key features					S.M.A Auto-Rea ata Clone Syste Embedd	lanagement A.R.T. d Refresh em (only for ML ed Mode ajor IC grades (optional)	-			
Operating temperature (°C)					Gold grade Diamond gra					
Storage temperature (°C)					-40	- 85				
Maximum transfer speed (MB/s)		up to 95 up to 80		up to 95 up to 90	Read: up to 20 Write: up to 20		ip to 95 ip to 80		up to 95 up to 90	Read: up to 6 Write: up to 5
Maximum power consumption (mA)					< 4	00				
MTBF					> 3 00	0 000				
Environmental tests resistance		High/Low temperature High Humidity (55, 95% RH) Temperature Cycle (30 min, 20 cycles) Shock(1 500 G, Half Sin Pulse) Vibration (80 – 2 000 Hz/20 G in 3 Axis) Free Fall (1.5 m) Torque (0.1 N/m, 30 sec/5 times) Bending (>10 N for 1 min/5 times) Salt Spray (3% NaCl, 35°C/24 h) Waterproof (IPX7, 1 m immersion for 30 minutes) X-Ray (70 – 140 keV for 30 minutes) Switch Cycle (0.4 – 0.5 N/1 000 times) Durability test (EIA 364–13 10 000 times) Contact ESD (±4 KV contact 25 times, ±8 KV air 10 times)								
Dimensions ((L × W × H) (mm))		15 × 11 × 1 32 × 24 × 2.1								

USB Flash Drive

USB Flash Drives are available in many housing options and with wide selection of NAND types (SLC, pSLC, MLC, 3D TLC). As the USB 3.2 gen. 1 interface is supported by nearly all personal computers and embedded applications, these devices are used as storage media for operating systems, data and application keys. Backwards compatibility with USB 2.0 and USB 1.1 provides flexibility for designers and administrators.



	Industrial USB Flash Drive										
Flash type	3D TLC	MLC	pSLC	SLC							
Capacity (PCBA)	16 GB – 256 GB	4 GB – 256 GB	128 MB – 32 GB								
Program/Erase cycles	3 000	3 000	20 000	60 000							
Interface		USB 2.0/USB 3.2 gen. 1 (USB 1.1/USB 2.0 compatible)									
Key features		Wear Leveling Bad Block Management ECC Build from major IC grades FIX BOM (optional) PCN and EOL notification									
Operating temperature (°C)		Carbon grade: 0 – 70 Silver grade: 0 – 70 Gold grade: -25 – 85 Diamond grade: -40 – 85									
Storage temperature (°C)		-40	- 85								
Maximum transfer speed (MB/s) (PCBA)	Read: up to 265 Write: up to 175	Read: up to 190 Write: up to 130	Read: up to 150 Write: up to 125	Read: up to 170 Write: up to 120							
Maximum power consumption (mA) (PCBA)	< 220	< 2	210	< 120							
Maximum transfer speed (MB/s) (uCOB)	Read: up to 220 Write: up to 100	Read: up to 190 Write: up to 85	Read: up to 140 Write: up to 100	Read: up to 65 Write: up to 50							
Maximum power consumption (mA) (uCOB)	< 187	< 1	30	< 90							
MTBF		> 2 00	0 000								
Environmental tests resistance		High/Low temperature High Humidity (55, 95% RH) Temperature Cycle (30 min, 20 cycles) Shock (1 500 G, Half Sin Pulse) Vibration (80 – 2 000 Hz/20 G in 3 Axis) Free Fall (1.1 m) Torque (0.5 N/m, 30 sec/5 times) Bending (>50 N for 1 min/5 times) Durability test (Extraction/Insertion 5 000 times) Contact ESD (±4 KV contact 25 times)									
Dimensions ((L × W × H) (mm))		55.8 × 18	3.6 × 9.6*								

*Dimensions for standard housing. Wide selection of housings is available.

2.5" SATA Solid State Drive

2.5" SATA is the most common form factor of Solid State Drives. All SSDs can be configured with 3D TLC, 3D pSLC, MLC, pSLC and SLC NAND Flash. They provide up to 550 MB/s of fast data transfer, low power consumption and advanced power management modes. With ruggedness resulting from absence of moving parts and low power consumption, Solid State Drives are optimal for both desktop and mobile applications.



	2.5" SATA Solid State Drive									
Flash type	3D TLC	3D pSLC	MLC	pSLC	SLC					
Program/Erase cycles	3 000	50 000	50 000 3 000 20 000							
Capacity	64 GB – 2 TB	32 GB – 512 GB	4 GB – 512 GB	8 GB – 256 GB	8 GB – 128 GB					
Interface			SATA III							
Key features		Static and Dynamic Wear Leveling Bad Block Management TRIM S.M.A.R.T. NCQ Over-provisioning Low Power Management Thermal Throttling DEVSLP Mode (optional) PLP (optional) Build from major IC grades FIX BOM (optional) PCN and EOL notification								
Operating temperature (°C)	Silver grade: 0 – 70 Diamond grade: -40 – 85	Silver grade: 0 – 70 Diamond grade: -40 – 85	Silver grad Gold grade Diamond gra	e: -25 – 85	Gold grade: -25 – 85 Diamond grade: -40 – 8					
Storage temperature (°C)			-40 - 85							
Maximum transfer speed (MB/s)	Read: up to 550 Write: up to 500	Read: up to 550 Write: up to 510	Read: up to 550 Write: up to 490	Read: up to 545 Write: up to 465	Read: up to 540 Write: up to 425					
Maximum power consumption (mW)	< 1 750	< 1 450	< 2 650	< 2 630	< 2 300					
MTBF	> 2 000 000	> 3 000 000		> 2 000 000						
Environmental tests resistance		High/Low temperature High Humidity (55, 95% RH) Temperature Cycle (30 min, 20 cycles) Shock (1 500 G, Half Sin Pulse) Vibration (80 – 2 000 Hz/20 G in 3 Axis) Free Fall (0.8 m) Torque (0.1 N/m, 30 sec/5 times) Bending (>20 N for 1 min/5 times) Contact ESD (±4 KV contact 25 times)								
Dimensions ((L × W × H) (mm))			100 × 69.85 × 7							

mSATA Solid State Drive

SSD mSATA is a type of Flash memory that can be installed directly on the motherboard. It is 80% smaller than the 2.5", thus it takes up minimal space. Compatibility with the SATA I, II and III standards means that these devices can be installed in any device having an mSATA port. As with the entire range of SSD memories, the absence of moving parts and low power consumption make it an optimum choice of data storage medium in mobile systems.



	mSATA Solid State Drive									
Flash type	3D TLC	3D pSLC	MLC	pSLC	SLC					
Program/Erase cycles	3 000	50 000	3 000	20 000	60 000					
Capacity	64 GB – 2 TB	32 GB – 512 GB	4 GB – 512 GB	2 GB – 512 GB	8 GB – 128 GB					
Interface			SATA III							
Key features	Static and Dynamic Wear Leveling Bad Block Management TRIM S.M.A.R.T. NCQ Over-Provisioning Low Power Management Thermal Throttling DEVSLP Mode (optional) Build from major IC grades FIX BOM (optional) PCN and EOL notification									
Work temprature (°C)		Silver grade: 0 – 70 Diamond grade: -40 – 85		Silver grade: 0 – 70 Gold grade: -25 – 85 Diamond grade: -40 – 85	Silver grade: 0 – 70 Diamond grade: -40 – 8					
Storage temperature (°C)			-40 - 85							
Maximum R/W (MB/s)		p to 550 p to 510		p to 550 p to 490	Read: up to 540 Write: up to 425					
Maximum power consumption (mW)	< 1 750	< 1 350	< 2	690	< 2 250					
MTBF	> 2 000 000	> 2 500 000		> 2 000 000						
Environment tests resistance	High/Low temperature High Humidity (55, 95% RH) Temperature Cycle (30 min, 20 cycles) Shock (1 500 G, Half Sin Pulse) Vibration (80 – 2 000 Hz/20 G in 3 Axis) Free Fall (0.8 m) Torque (0.1 N/m, 30 sec/5 times) Bending (>20 N for 1 min/5 times) Contact ESD (±4 KV contact 25 times)									
Dimensions ((L × W × H) (mm))	50.8 × 29.85 × 4									

M.2 SATA / NVMe Solid State Drive

M.2 is another type of SSD with SATA or NVMe interface. M.2 SATA Solid State Drive can be installed directly onto motherboard. It can be configured with 3D TLC, 3D pSLC, MLC, pSLC and SLC NAND and PCBA can be delivered in two sizes: 42 x 22 mm and 80 x 22 mm. Small footprint, lack of moving parts and low power consumption make M.2 SATA SSD a great solution for mobile applications. Other form factors (2260, 22110) available upon request.





	M.2 SATA Solid State I											
Form factor			M.2 2242			M.2 2280						
Flash type	3D TLC	3D TLC 3D pSLC MLC pSLC SLC				3D TLC	3D pSLC	MLC	pSLC	SLC		
Program/Erase cycles	3 000	50 000	3 000	20 000	60 000	3 000	50 000	3 000	20 000	60 000		
Capacity	64 GB - 1 TB	32 GB – 256 GB	4 GB – 512 GB	16 GB – 256 GB	8 GB – 64 GB	64 GB – 2 TB	32 GB - 512 GB	4 GB – 512 GB	2 GB – 256 GB	8 GB – 128 G		
Interface					SAT	TA III						
Key features	Over	Static and Dynamic Wear Leveling - Bad Block Management - TRIM - S.M.A.R.T NCQ Over-provisioning - Low Power Management - Thermal Throttling - DEVSLP Mode (optional) - PLP (optional) Build from major IC grades - FIX BOM (optional) - PCN and EOL notification										
Operating temperature (°C)	Silver grade: 0 – 70 Diamond grade: -40 – 85			Gold grade: -25 – 85 Diamond grade: -40 – 85	85 0 – 70 Gold grade: 0 – 70 - I grade: Diamond grade: -25 – 85 Diamond grade: Diam			Gold grade: -25 – 85 Diamond grade -40 – 85				
Storage temperature (°C)					-40	- 85						
Maximum transfer speed (MB/s)	up to Wr	ead: o 550 rite: o 510	Read: up to 555 Write: up to 490	Read: up to 545 Write: up to 460	Read: up to 540 Write: up to 320	Read: up to 550 Write: up to 510		Read: up to 550 Write: up to 490		Read: up to 540 Write: up to 425		
Max. power consumption (mW)	< 1 750	< 1 350	< 2 100	< 2 630	< 1 950	< 1 800	< 1 300	< 2	650	< 2 280		
MTBF	> 2 000 000	000 > 3 000 000 > 2 000 000					> 3 000 000 > 2 000 000					
Environmental tests resistance		High/Low temperature, High Humidity (55, 95% RH), Temperature Cycle (30 min, 20 cycles), Shock (1 500 G, Half Sin Pulse), Vibration (80 – 2 000 Hz/20 G in 3 Axis), Free Fall (0.8 m), Torque (0.1 N/m, 30 sec/5 times), Bending (>20 N for 1 min/5 times), Contact ESD (±4 KV contact 25 times)										
Dimensions ((L×W×H) (mm))			42 × 22 × 3.8					80 × 22 × 3.8				

	M.2 NVMe Solid State Drive									
Interface		NVMe F	PCIe 4x4		NVMe PCIe 3x4					
Form factor	M.2 2230	2230 M.2 2242 M.2 2280			M.2	2242	M.2 2280			
Flash type	3D TLC 3D TLC			3D pSLC	3D TLC	3D pSLC	3D TLC	3D pSLC		
Program/Erase cycles	3 0	00	3 000	50 000	3 000	50 000	3 000	50 000		
Capacity	256 GB – 512 GB	128 GB – 2 TB	128 GB – 2 TB	120 GB – 960 GB	128 GB – 2 TB	32 GB – 512 GB	128 GB – 2 TB	32 GB – 512 GB		
Advanced features	Read Only Mode Build from major IC grades FIX BOM (optional) PCN and EOL notification			TCG Pyrite/Opal (optional) NVME Format Physical Presence (SID) (optional) Manufacturer's Secure ID (MSID) Sanitize Operation Read Only Mode Build from major IC grade FIX BOM (optional) PCN and EOL notificatio	Secure Eras Read Only PLP (c FIX BON					
Operating temperature (°C)		- 0 Diamon	grade: - 70 d grade: – 85		Silver grade: 0 – 70	Silver grade: 0 – 70 Diamond grade: -40 – 85	Silver grade: 0 – 70	Silver grade: 0 – 70 Diamond grade -40 – 85		
Storage temperature (°C)				-40 -	- 85					
Maximum transfer speed (MB/s)	Read: up to 4 900 Write: up to 3 200		o to 4 900 o to 3 700	Read: up to 7 200 Write: up to 6 500		Read: up to 2 450 Write: up to 1 900				
Max. power consumption (mW)	< 5 200	< 5	300	< 11 000	< 3	900	< 4	000		
MTBF				> 2 00	0 000					
Dimensions ((L × W × H) (mm))	30 × 22 × 2.15	42 × 22 × 3.8	80 × 22 × 3.8	80 × 22 × 1.35	42 × 22 × 3.8		80 × 22 × 3.8			

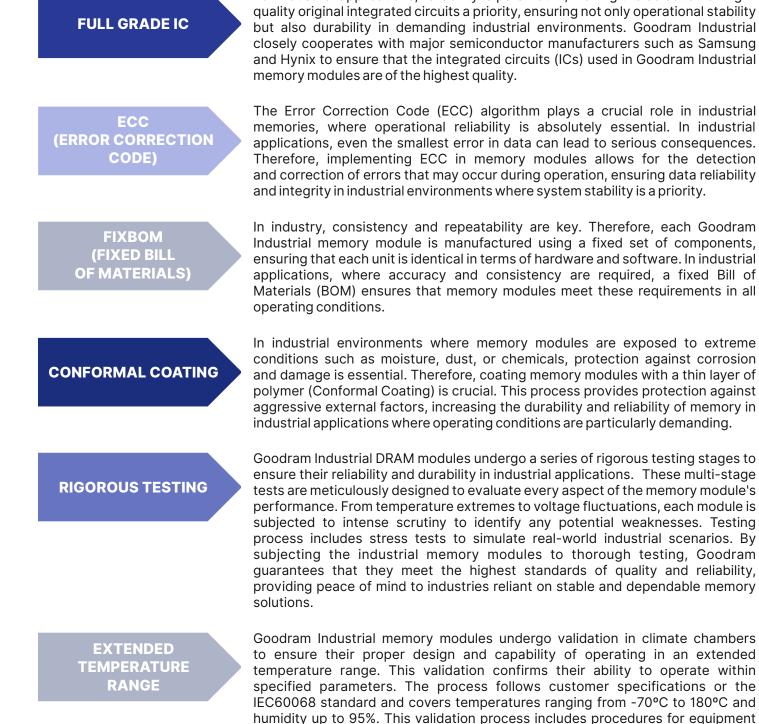
DRAM core features

DRAM MODULES

Goodram Industrial memory leverage state-of-the-art technologies to uphold unparalleled reliability. These features stand as the cornerstone of industrial memory, underlining their paramount significance in ensuring uninterrupted operations in industrial settings. The utilization of advanced technologies underscores the critical role memory plays in industrial environments, where system stability and data integrity are non-negotiable. By prioritizing reliability, Goodram Industrial memory modules become indispensable components, capable of withstanding the rigorous demands of industrial applications. Their reliability is not just a feature but a fundamental necessity, safeguarding against potential disruptions

and downtime in industrial processes.

The technologies used in our memory modules include:



For industrial applications, reliability is paramount, making the selection of highquality original integrated circuits a priority, ensuring not only operational stability but also durability in demanding industrial environments. Goodram Industrial closely cooperates with major semiconductor manufacturers such as Samsung and Hynix to ensure that the integrated circuits (ICs) used in Goodram Industrial

The Error Correction Code (ECC) algorithm plays a crucial role in industrial memories, where operational reliability is absolutely essential. In industrial applications, even the smallest error in data can lead to serious consequences. Therefore, implementing ECC in memory modules allows for the detection and correction of errors that may occur during operation, ensuring data reliability and integrity in industrial environments where system stability is a priority.

In industry, consistency and repeatability are key. Therefore, each Goodram Industrial memory module is manufactured using a fixed set of components, ensuring that each unit is identical in terms of hardware and software. In industrial applications, where accuracy and consistency are required, a fixed Bill of Materials (BOM) ensures that memory modules meet these requirements in all

In industrial environments where memory modules are exposed to extreme conditions such as moisture, dust, or chemicals, protection against corrosion and damage is essential. Therefore, coating memory modules with a thin layer of polymer (Conformal Coating) is crucial. This process provides protection against aggressive external factors, increasing the durability and reliability of memory in industrial applications where operating conditions are particularly demanding.

Goodram Industrial DRAM modules undergo a series of rigorous testing stages to ensure their reliability and durability in industrial applications. These multi-stage tests are meticulously designed to evaluate every aspect of the memory module's performance. From temperature extremes to voltage fluctuations, each module is subjected to intense scrutiny to identify any potential weaknesses. Testing process includes stress tests to simulate real-world industrial scenarios. By subjecting the industrial memory modules to thorough testing, Goodram guarantees that they meet the highest standards of quality and reliability, providing peace of mind to industries reliant on stable and dependable memory

preparation and software verification tailored to customer needs.

DRAM

Goodram Industrial offers a comprehensive range of industrial memory modules spanning from the early DDR1 generation to the latest DDR5 technology. Within its industrial series, the brand provides a variety of form factors including long DIMMs or SODIMMs, along with optional features such as ECC support, extended temperature range capabilities, and a fixed bill of materials. Goodram Industrial prioritizes adherence to the Product Change Notification procedure, ensuring that clients are informed of any alterations to the bill of materials, particularly for orders spanning extended durations. Its tailored solutions cater to a diverse array of industrial applications including industrial computing, automation, automotive systems, home automation, point-of-sale (POS) systems, Internet of Things (IoT), and healthcare applications.



DDR5 SDRAM

The latest advancement in the DDR family, DDR5 boasts a maximum transfer speed of 6 400 MT/s, achieved by lowering the voltage to 1.1 V, reducing overall power consumption by up to 15%. Incorporating a power management IC (PMIC) on the module and implementing on-die error-correction code (ODECC) enhances reliability and efficiency. Additionally, DDR5 introduces two sets of 32-bit channels (40-bit for ECC modules), doubling the bandwidth for improved memory access speed and efficiency in industrial environments.

DDR5 DIMM





	DDR5 Memory Modules								
Module type	UDIMM	UDIMM UDIMM ECC SODIMM							
Capacity	8 GB – 32 GB	16 GB – 32 GB	8 GB – 32 GB	16 GB – 32 GB					
Data Rate	4 800 MT/s 5 200 MT/s 5 600 MT/s 6 400 MT/s	4 800 MT/s 5 200 MT/s 5 600 MT/s 6 400 MT/s	4 800 MT/s 5 200 MT/s 5 600 MT/s 6 400 MT/s	4 800 MT/s 5 200 MT/s 5 600 MT/s 6 400 MT/s					
Number of pins	288-pin	288-pin	262-pin	262-pin					
Width	64 Bits	72 Bits	64 Bits	72 Bits					
Voltage	1.1	V	1.1 V						
PCB Height	31.25	mm	30 mm						
Operating temperature (°C)	0 - 8	85	0 -	85					
Extended temperature* (°C)	-40 -	- 85	-40 - 85						
On Die ECC	Yes	Yes	Yes	Yes					
Power Management IC	Yes	Yes	Yes	Yes					
FIX BOM	*	*	*	*					
EOL, PCN notification	Yes	Yes	Yes	Yes					
Conformal Coating	*	*	*	*					

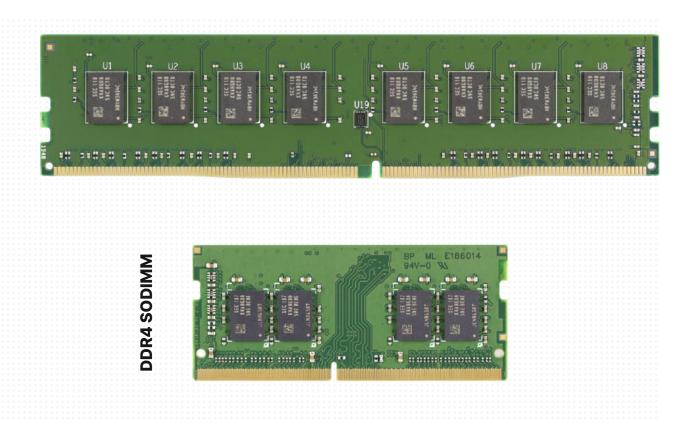
*optional

DRAM



DDR4 SDRAM

Currently the most prevalent type, DDR4 introduced innovative features such as a POD12 interface and CRC on the data bus, enabling transfer rates exceeding 3 200 MT/s. With transfer rates up to 25 600 MB/s, DDR4 became an ideal choice for high-performance industrial systems, prioritizing speed and reliability.



	DDR4 Memory Modules				
Module type	UDIMM	UDIMM ECC	SODIMM	SODIMM ECC	
Capacity	4 GB – 32 GB				
Data Rate	2 133 MT/s 2 400 MT/s 2 666 MT/s 2 933 MT/s 3 200 MT/s	2 133 MT/s 2 400 MT/s 2 666 MT/s 2 933 MT/s 3 200 MT/s	2 133 MT/s 2 400 MT/s 2 666 MT/s 2 933 MT/s 3 200 MT/s	2 133 MT/s 2 400 MT/s 2 666 MT/s 2 933 MT/s 3 200 MT/s	
Number of pins	288-pin	288-pin	260-pin	260-pin	
Width	64 Bits	72 Bits	64 Bits	72 Bits	
Voltage	1.2 V		1.2 V		
PCB Height	31.25 mm		30 mm		
PCB VLP Height*	19 mm		19 mm		
Operating temperature (°C)	0 - 85		0 - 85		
Extended temperature* (°C)	-40 - 85		-40 - 85		
FIX BOM	*	*	*	*	
EOL, PCN notification	Yes	Yes	Yes	Yes	
Conformal Coating	*	*	*	*	

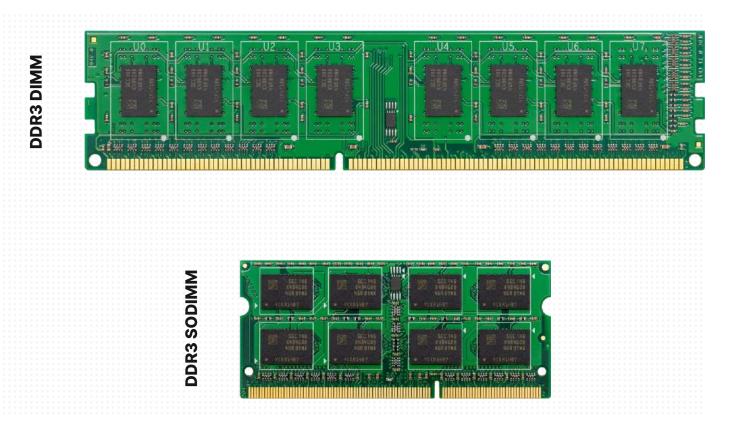
*optional

DRAM



DDR3 SDRAM

DDR3 marked a significant leap forward, offering lower power consumption and higher capacity for a wide range of industrial applications. With transfer rates of 1 866 MT/s facilitated by a "fly-by" bus design, DDR3 optimized performance while meeting industrial demands.



	DDR3 Memory Modules			
Module type	UDIMM	UDIMM ECC	SODIMM	SODIMM ECC
Capacity	2 GB – 8 GB			
Data Rate	1 066 MT/s 1 333 MT/s 1 600 MT/s 1 866 MT/s	1 066 MT/s 1 333 MT/s 1 600 MT/s 1 866 MT/s	1 066 MT/s 1 333 MT/s 1 600 MT/s 1 866 MT/s	1 066 MT/s 1 333 MT/s 1 600 MT/s 1 866 MT/s
Number of pins	240-pin	240-pin	204-pin	204-pin
Width	64 Bits	72 Bits	64 Bits	72 Bits
Voltage	1.35 V, 1.5 V		1.35 V, 1.5 V	
PCB Height	30 mm		30 mm	
Operating temperature (°C)	0 - 85		0 - 85	
Extended temperature (°C)	-40 - 85		-40 - 85	
FIX BOM	*	*	*	*
EOL, PCN notification	Yes	Yes	Yes	Yes
Conformal Coating	*	*	*	*

*optional



DDR2 SDRAM

The second generation brought improvements in power consumption by operating at reduced supply voltage. Running at a data rate of 800 MT/s, DDR2 achieved transfer rates of up to 6 400 MB/s, enhancing efficiency while maintaining compatibility.



	DDR2 Memory Modules		
Module type	UDIMM	SODIMM	
Capacity	512 MB – 2 GB	512 MB – 2 GB	
Data Rate	400 MT/s, 533 MT/s, 667 MT/s, 800 MT/s	400 MT/s, 533 MT/s, 667 MT/s, 800 MT/s	
Number of pins	240-pin	200-pin	
Width	64 Bits		
Voltage	1.8 V		
PCB Height	30 mm	30 mm	
Operating temperature (°C)	0 – 85		
FIX BOM	*	*	
EOL, PCN notification	Yes	Yes	
Conformal Coating	* *		

*optional



DDR1 SDRAM

The first member of the DDR family introduced a synchronous interface active on both edges of the clock signal. With a data rate of 400 MT/s and a transfer rate of 3 200 MB/s over a 64-bit bus, DDR1 laid the foundation for subsequent generations.

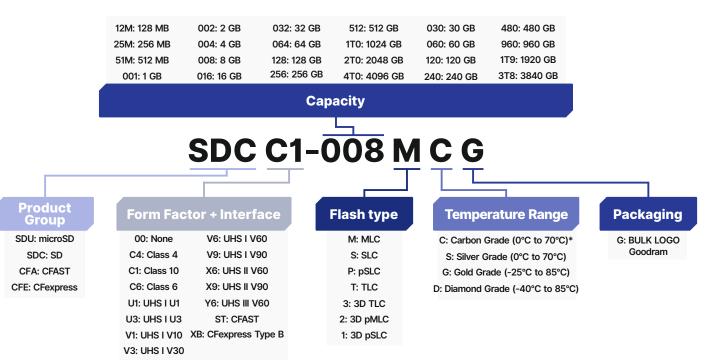


	DDR1 Memory Modules		
Module type	UDIMM	SODIMM 128 MB – 1 GB	
Capacity	128 MB – 1 GB		
Data Rate	200 MT/s, 266 MT/s, 333 MT/s, 400 MT/s	200 MT/s, 266 MT/s, 333 MT/s, 400 MT/s	
Number of pins	184-pin	144-pin	
Width	64 Bits		
Voltage	2.5 V		
PCB Height	29.50 mm	31.75 mm	
Operating temperature (°C)	0 – 70		
FIX BOM	*	*	
EOL, PCN notification	Yes	Yes	
Conformal Coating	*	*	

Part number decoder

Flash Memory (Memory Cards)

(SD, microSD, CFast, CFexpress)



USB Flash Drives

12M: 128 MB	002: 2 GB	032: 32 GB	030: 30 GB
25M: 256 MB	004: 4 GB	064: 64 GB	060: 60 GB
51M: 512 MB	008: 8 GB	128: 128 GB	120: 120 GB
001: 1 GB	016: 16 GB	256: 256 GB	240: 240 GB

Capacity

UOP <u>30</u>-008 M C G



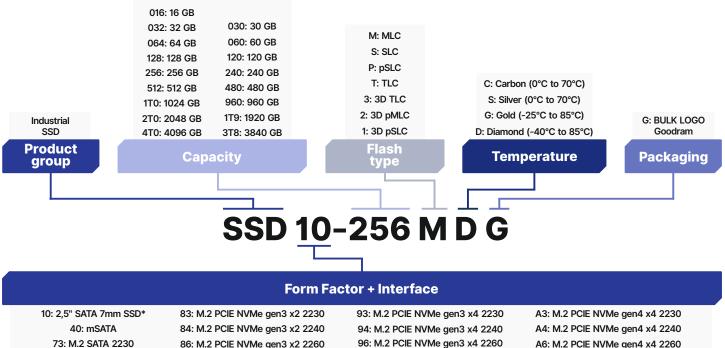
Packaging

G: Goodram BULK B: OEM BULK L: Goodram BULK LOGO

Part number decoder

Flash Memory (SSD)

(2,5" SATA, mSATA, M.2 SATA, M.2 PCIe)



76: M.2 SATA 2260 78: M.2 SATA 2280 71: M.2 SATA 22110

74: M.2 SATA 2242

86: M.2 PCIE NVMe gen3 x2 2260 88: M.2 PCIE NVMe gen3 x2 2280 81: M.2 PCIE NVMe gen3 x2 22110

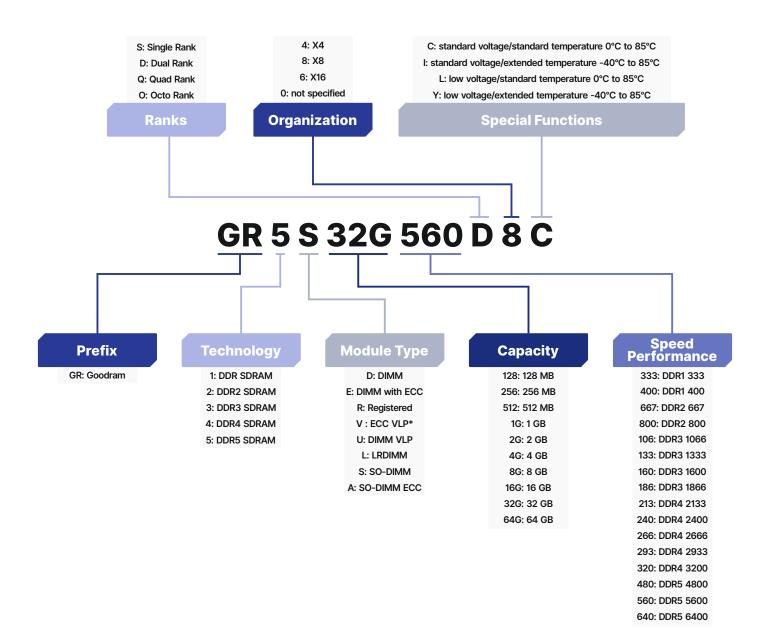
96: M.2 PCIE NVMe gen3 x4 2260 98: M.2 PCIE NVMe gen3 x4 2280 91: M.2 PCIE NVMe gen3 x4 22110

A6: M.2 PCIE NVMe gen4 x4 2260 A8: M.2 PCIE NVMe gen4 x4 2280 A1. M.2 PCIE NVMe gen4 x4 22110

Part number decoder

DRAM Memory

(UDIMM, SODIMM)



* VLP - Very Low Profile



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